



2N1671 – 2N1671A – 2N1671B

PN BAR-TYPE SILICON UNIJUNCTION TRANSISTORS

The 2N1671, 2N1671A AND 2N1671B are mounted in TO-5 metal package. They are designed for medium power switching, oscillator and pulse timing circuit.

- Highly Stable Negative Resistance and Firing Voltage
- Low Firing Current
- High Pulse Current Capabilities
- Simplified Circuit Design

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

| Symbol | Ratings | Value | Unit | |
|------------|----------------------------------|---------|-------------|----|
| V_{B1E} | Base 1 – Emitter Reverse Voltage | 2N1671 | 30 | V |
| | | 2N1671A | | |
| | | 2N1671B | | |
| V_{B2E} | Base 2 – Emitter Reverse Voltage | 2N1671 | 30 | V |
| | | 2N1671A | | |
| | | 2N1671B | | |
| V_{B1B2} | Interbase Voltage | 2N1671 | 35 | V |
| | | 2N1671A | | |
| | | 2N1671B | | |
| I_{FRMS} | RMS Emitter Current | 2N1671 | 50 | mA |
| | | 2N1671A | | |
| | | 2N1671B | | |
| I_{EM} | Emitter Peak Current | 2N1671 | 2 | A |
| | | 2N1671A | | |
| | | 2N1671B | | |
| P_{TOT} | Total Power Dissipation | 2N1671 | 450 | mW |
| | | 2N1671A | | |
| | | 2N1671B | | |
| T_J | Maximum Junction | 2N1671 | 150 | °C |
| | | 2N1671A | | |
| | | 2N1671B | | |
| T_{STG} | Storage Temperature Range | 2N1671 | -55 to +150 | |
| | | 2N1671A | | |
| | | 2N1671B | | |



2N1671 – 2N1671A – 2N1671B

ELECTRICAL CHARACTERISTICS

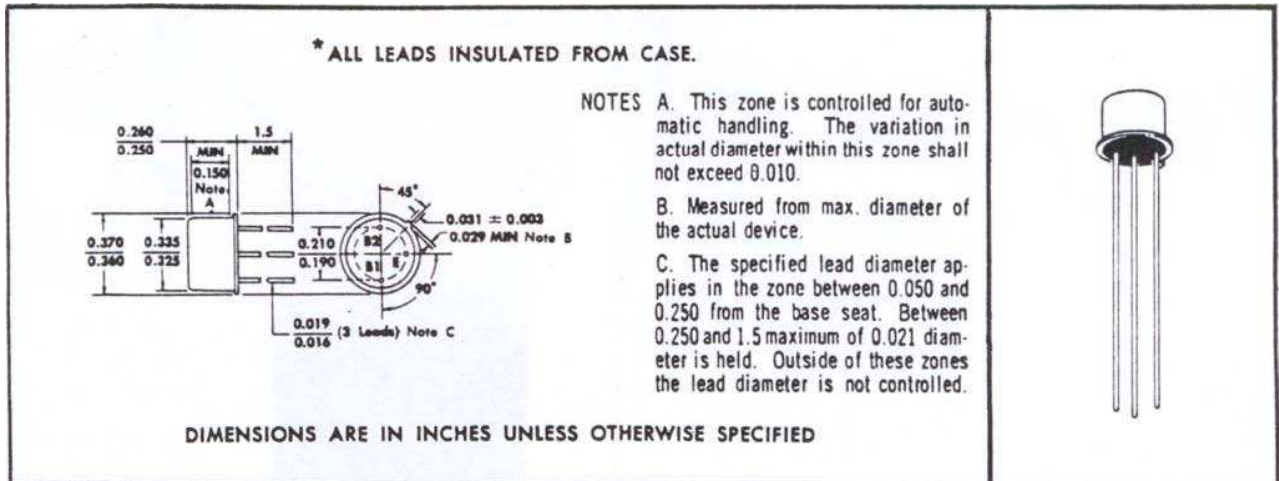
TC=25°C unless otherwise noted

| Symbol | Ratings | Test Condition(s) | Min | Typ | Max | Unit | |
|----------------|----------------------------|--|---------|------|-----|------|---------------|
| I_{EB2O} | Emitter Reverse Current | $V_{B2E}=30\text{ V}, I_{B1}=0$ | 2N1671 | - | - | -12 | μA |
| | | | 2N1671A | - | - | -12 | |
| | | | 2N1671B | - | - | -0.2 | |
| $V_{EB1(sat)}$ | Emitter saturation Voltage | $V_{B2B1} = 10\text{ V}, I_E = 50\text{ mA}$ | 2N1671 | - | - | 5 | V |
| | | | 2N1671A | | | | |
| | | | 2N1671B | | | | |
| R_{BBO} | Interbase Resistance | $V_{B2B1} = 3\text{ V}, I_E = 0$ | 2N1671 | 4.7 | - | 9.1 | K Ω |
| | | | 2N1671A | | | | |
| | | | 2N1671B | | | | |
| η | Intrinsic stand-off ratio | $V_{B2B1} = 10\text{ V}$ | 2N1671 | 0.47 | - | 0.62 | - |
| | | | 2N1671A | | | | |
| | | | 2N1671B | | | | |
| I_v | Valley Current | $V_{B2B1} = 10\text{ V}$ $R_{B2} = 100\ \Omega$ | 2N1671 | - | - | 8 | mA |
| | | | 2N1671A | | | | |
| | | | 2N1671B | | | | |
| I_P | Peak Current | $V_{B2B1} = 25\text{ V}$ | 2N1671 | - | - | 25 | μA |
| | | | 2N1671A | | | 25 | |
| | | | 2N1671B | | | 6 | |



2N1671 – 2N1671A – 2N1671B

MECHANICAL DATA CASE TO-5



Revised October 2012

Information furnished is believed to be accurate and reliable. However, Comset Semiconductors assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. Data are subject to change without notice. Comset Semiconductors makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Comset Semiconductors assume any liability arising out of the application or use of any product and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Comset Semiconductors' products are not authorized for use as critical components in life support devices or systems.

www.comsetsemi.com

info@comsetsemi.com

COMSET SEMICONDUCTORS

3 | 3